Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	2	patterned film and wet-processing and organic solvent	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/03/04 13:58
S2	440	patterned film and organic solvent	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/01/12 10:37
S3	3	patterned film and wet-processing	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/01/12 10:34
S4	62	patterned film and organic solvent and cleaning	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/01/12 10:59
S5	3	patterned film and organic solvent same wet etching	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/01/12 11:15
S6	1	patterned film and isopropyl alcohol same wet etching	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/01/12 12:12
S7	3366	semiconductor substrate and organic solvent	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/01/12 12:18
S8	5	semiconductor substrate and organic solvent and wet-processing	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/01/12 12:20

S9	471	semiconductor substrate and organic solvent and wet etching	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/01/12 12:23
S10	43	semiconductor substrate and organic solvent same wet etching	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/01/12 12:24
S11	17	high-k and organic solvent	USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/03/02 18:23
S12	152	wet etch\$4 same organic solvent	USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/03/02 18:25
S13	4	wet etch\$4 same organic solvent and gate dielectric	USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/03/02 18:28
S14	35	wet etch\$4 same high-k	USPAT; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/03/02 18:29
S15	25	high-k and isopropyl alcohol	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/03/04 16:09
S16	13	high-k same etching and isopropyl alcohol	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/03/04 16:26
S17	18	high-k same etching same organic	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2005/03/04 16:29
S18	2	"6855639".pn.	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/20 13:49

S19	1	("6300202").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/09/20 17:31
S20	59	high-k same dry adj etching	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/20 17:32